

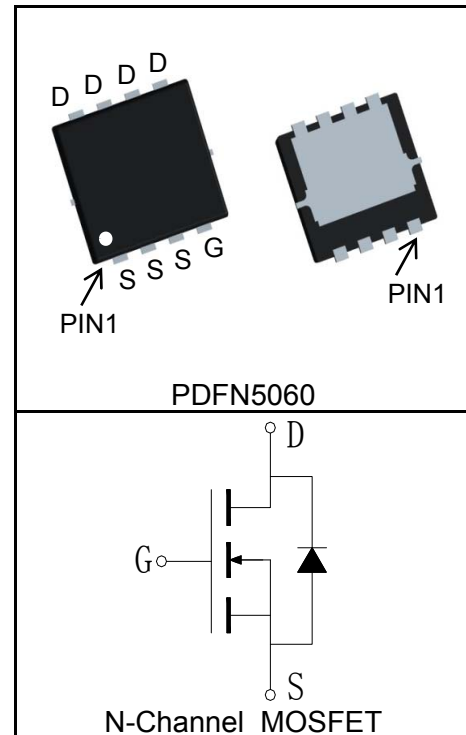
Features

- 60V/80A,
- $R_{DS(ON)} = 6m\Omega(Typ.)@V_{GS}=10V$
- $R_{DS(ON)} = 6.5m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- Fast Switching Speed
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Power Management.
- Switch Applications.
- Load switch.

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage	60	V	
V_{GSS}	Gate-Source Voltage	± 20		
T_J	Maximum Junction Temperature	150	$^\circ C$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$	
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$	50	A
Mounted on Large Heat Sink				
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$	320	A
$I_D^{②}$	Continuous Drain Current@ $T_C(V_{GS}=10V)$	$T_C=25^\circ C$	80	A
		$T_C=100^\circ C$	50	
	Continuous Drain Current@ $T_A(V_{GS}=10V)^{③}$	$T_A=25^\circ C$	21	
		$T_A=70^\circ C$	16	
P_D	Maximum Power Dissipation@ T_C	$T_C=25^\circ C$	62.5	W
		$T_C=100^\circ C$	25	
	Maximum Power Dissipation@ $T_A^{③}$	$T_A=25^\circ C$	4.2	
		$T_A=70^\circ C$	2.7	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2	°C/W
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	30	°C/W
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	196	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU6085M			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1		2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=35A$		6	7	$m\Omega$
		$V_{GS}=10V, I_{DS}=50A$		6.5	8	$m\Omega$
Diode Characteristics						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=50A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=50A, dI_{SD}/dt=100A/\mu s$		38		ns
Q_{rr}	Reverse Recovery Charge			72		nC
Dynamic Characteristics ⁽⁶⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.2		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		3450		pF
C_{oss}	Output Capacitance			310		
C_{rss}	Reverse Transfer Capacitance			115		
$t_{d(ON)}$	Turn-on Delay Time			28		
t_r	Turn-on Rise Time	$V_{DD}=30V, I_{DS}=50A,$ $V_{GEN}=10V, R_G=4.7\Omega$		32		
$t_{d(OFF)}$	Turn-off Delay Time			98		
t_f	Turn-off Fall Time			68		
Gate Charge Characteristics ⁽⁶⁾						
Q_g	Total Gate Charge	$V_{DS}=48V, V_{GS}=10V,$ $I_{DS}=50A$		75		nC
Q_{gs}	Gate-Source Charge			19		
Q_{gd}	Gate-Drain Charge			26		

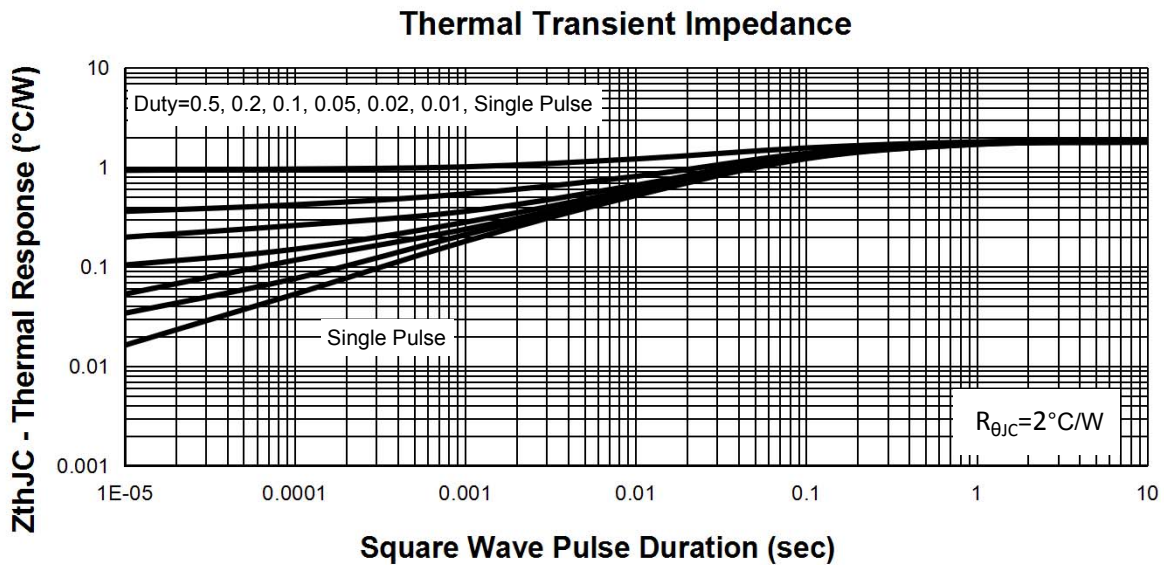
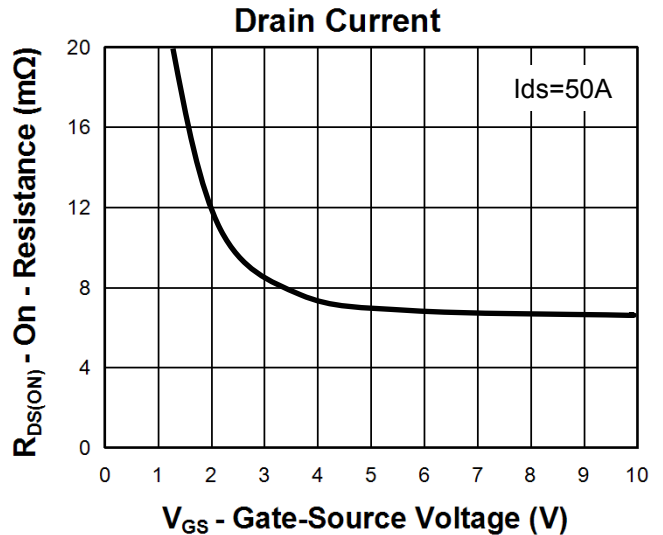
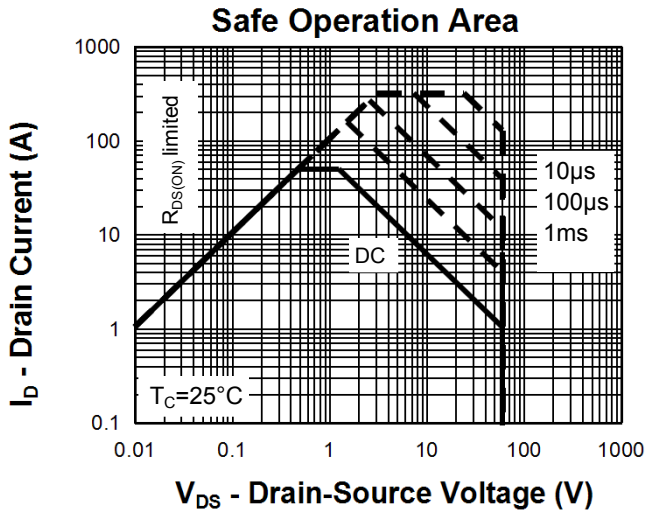
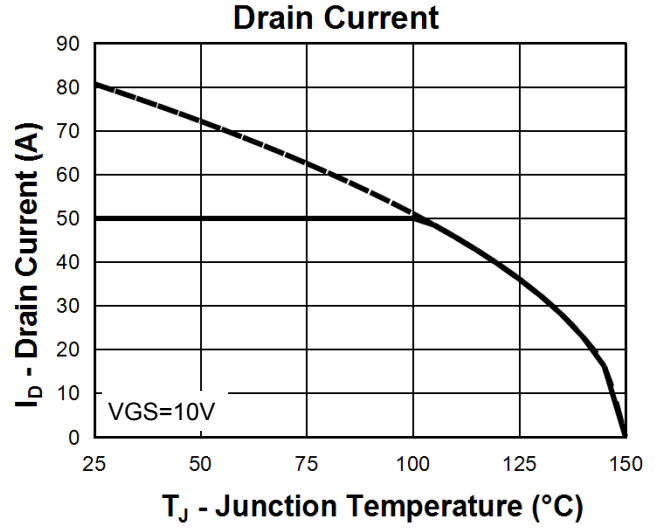
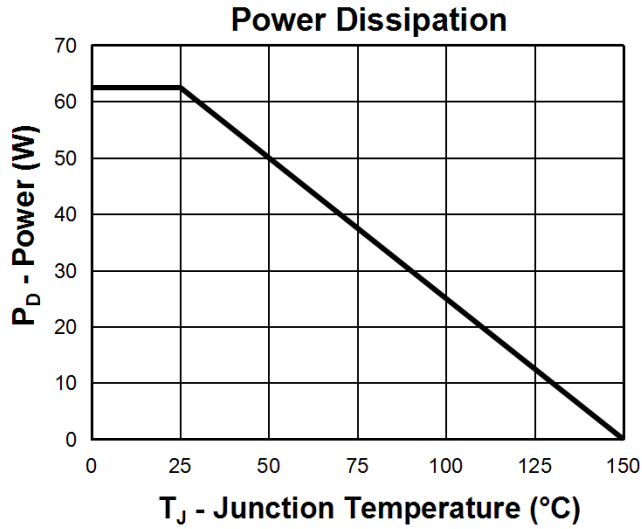
Notes:

- ① Max current is limited to 50A by the package.
- ② Pulse width limited by safe operating area.
- ③ When mounted on 1 inch square copper board, t 10sec.
- ④ Limited by TJmax, IAS =28A, VDD =24V, RG = 50Ω , Starting TJ = 25° C.
- ⑤ Pulse test ; Pulse width300s, duty cycle2%.
- ⑥ Guaranteed by design, not subject to production testing.

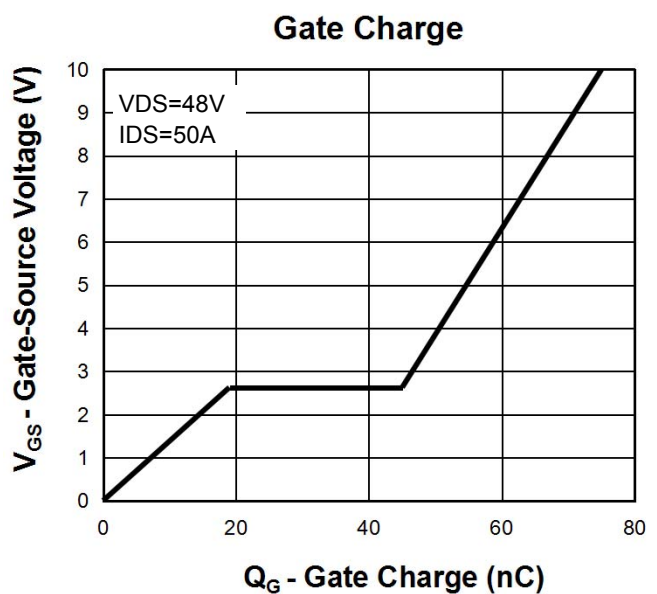
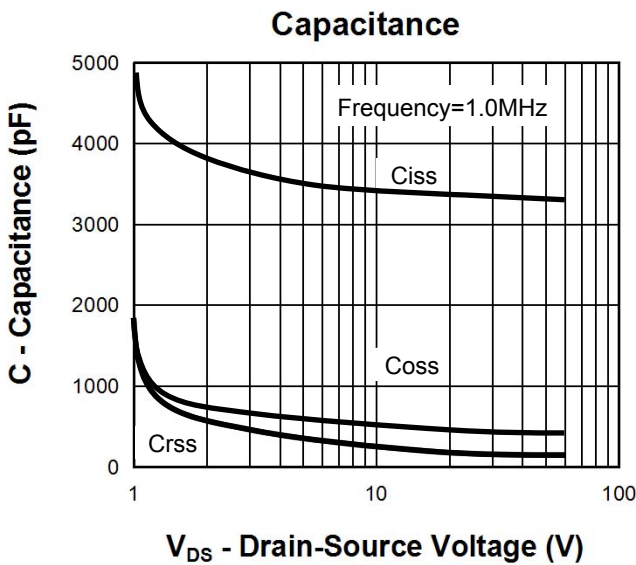
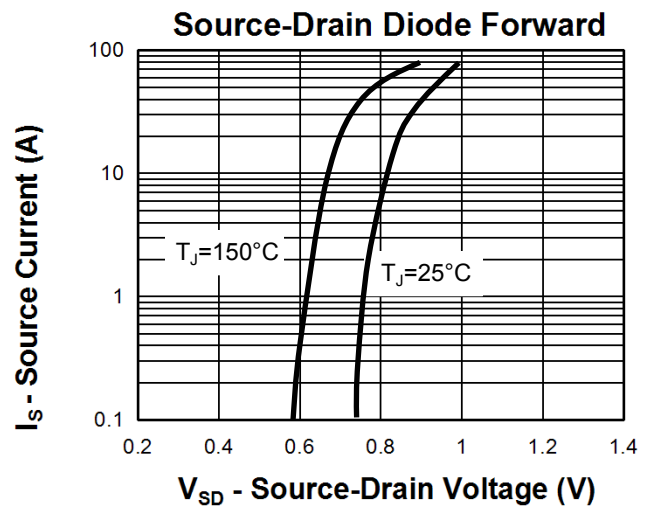
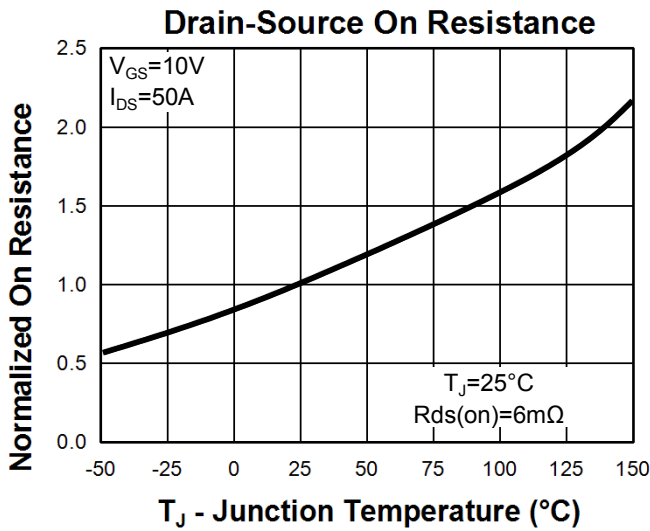
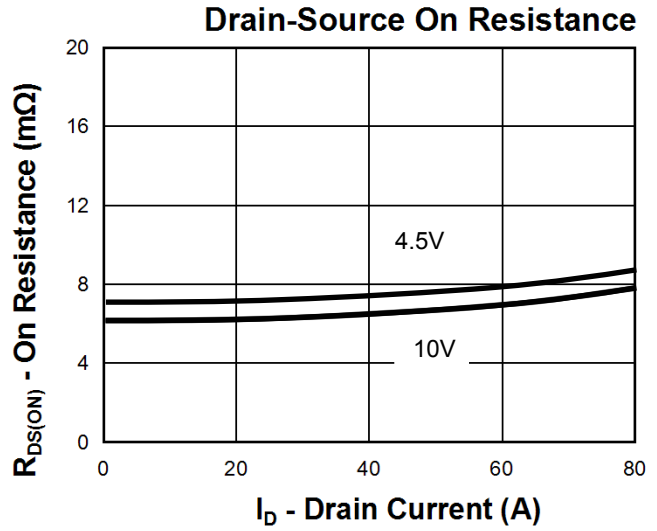
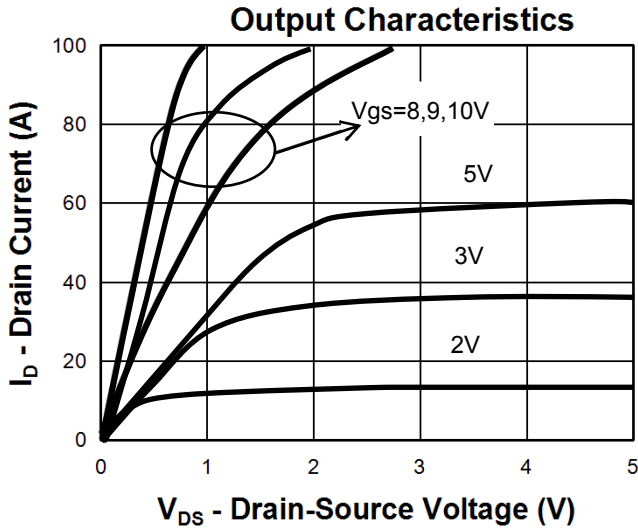
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU6085M	RU6085M	PDFN5060	Tape&Reel	3000	13"	12mm

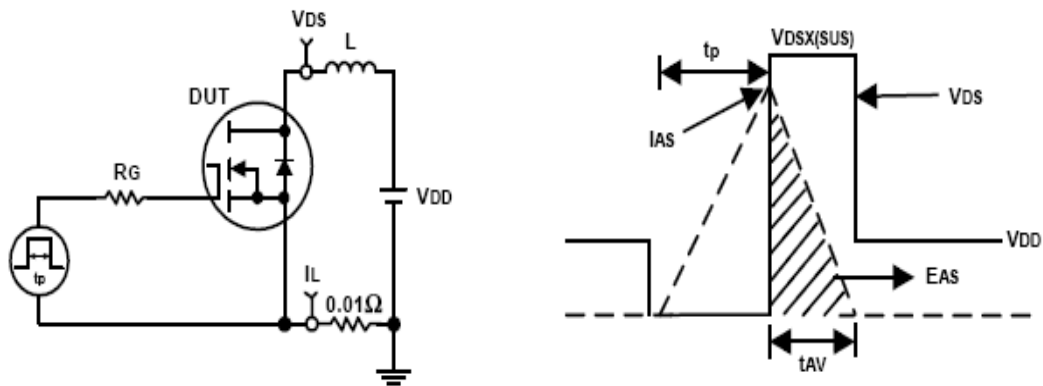
Typical Characteristics



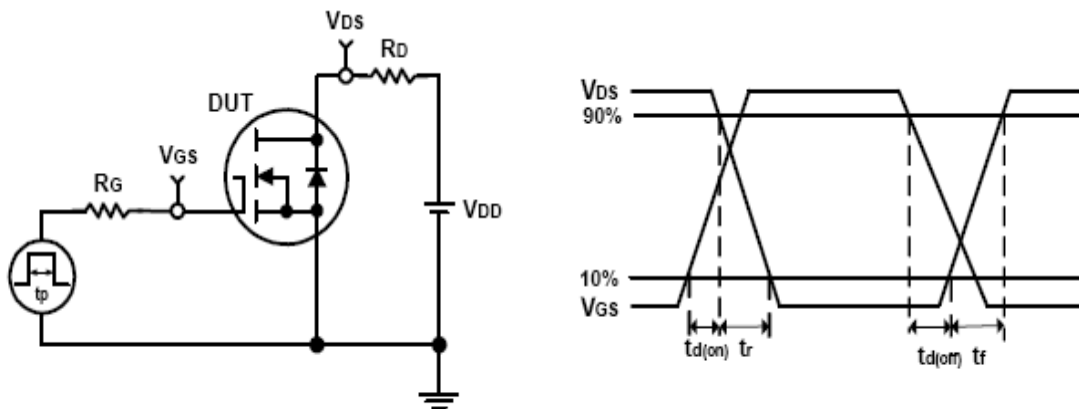
Typical Characteristics



Avalanche Test Circuit and Waveforms

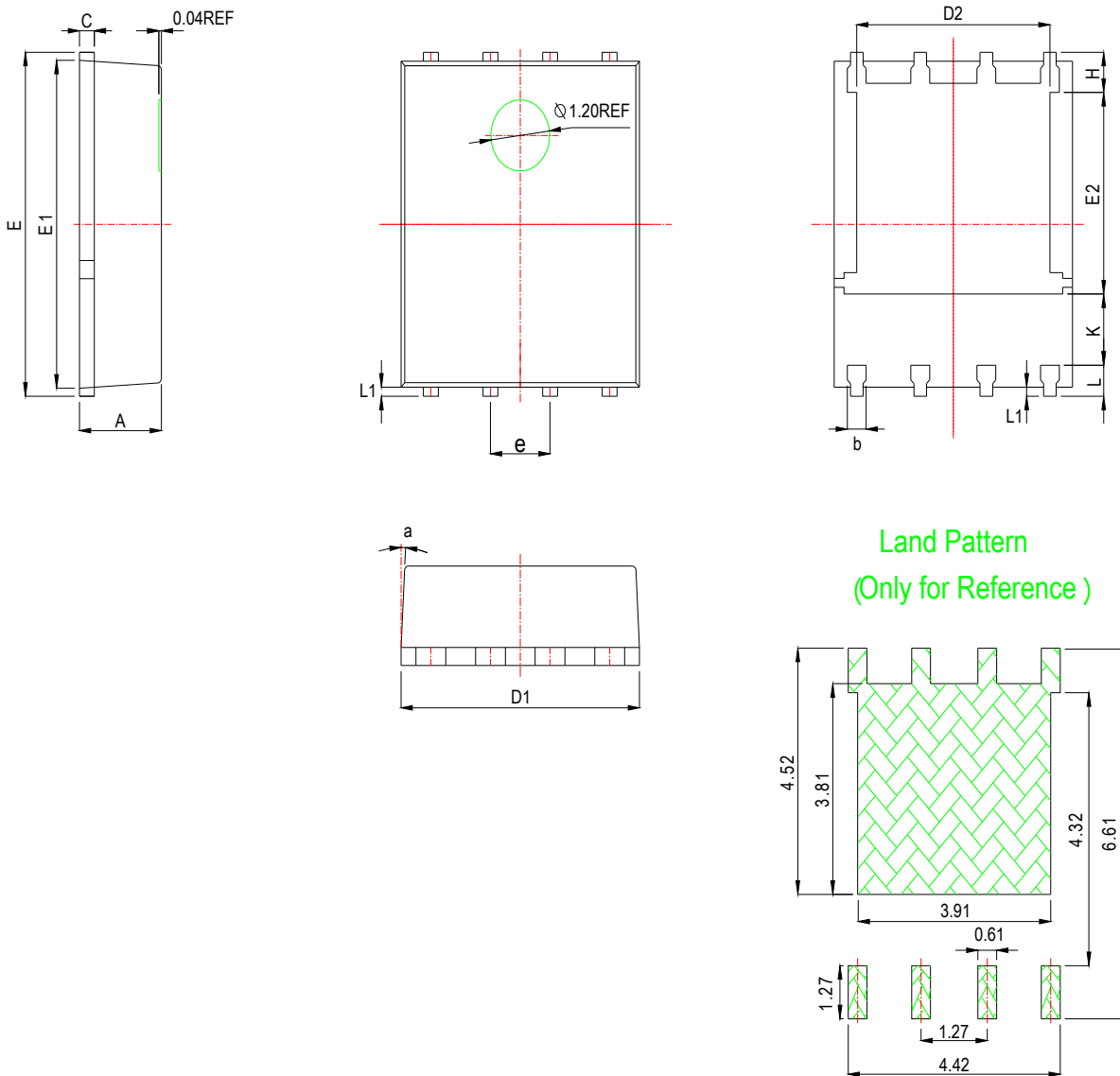


Switching Time Test Circuit and Waveforms



Package Information

PDFN5060



Land Pattern
(Only for Reference)

SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
b	0.33	0.42	0.51	0.013	0.017	0.020
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.61	3.79	3.96	0.142	0.149	0.156
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	5.65	5.75	5.85	0.222	0.226	0.230
E2	3.38	3.58	3.78	0.133	0.141	0.149
e	1.27 BSC			0.005 BSC		
H	0.41	0.51	0.61	0.016	0.020	0.024
k	1.10			0.043		
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
a	0°		12°	0°		12°

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